

## isc Silicon PNP Power Transistor

2SA2040

## DESCRIPTION

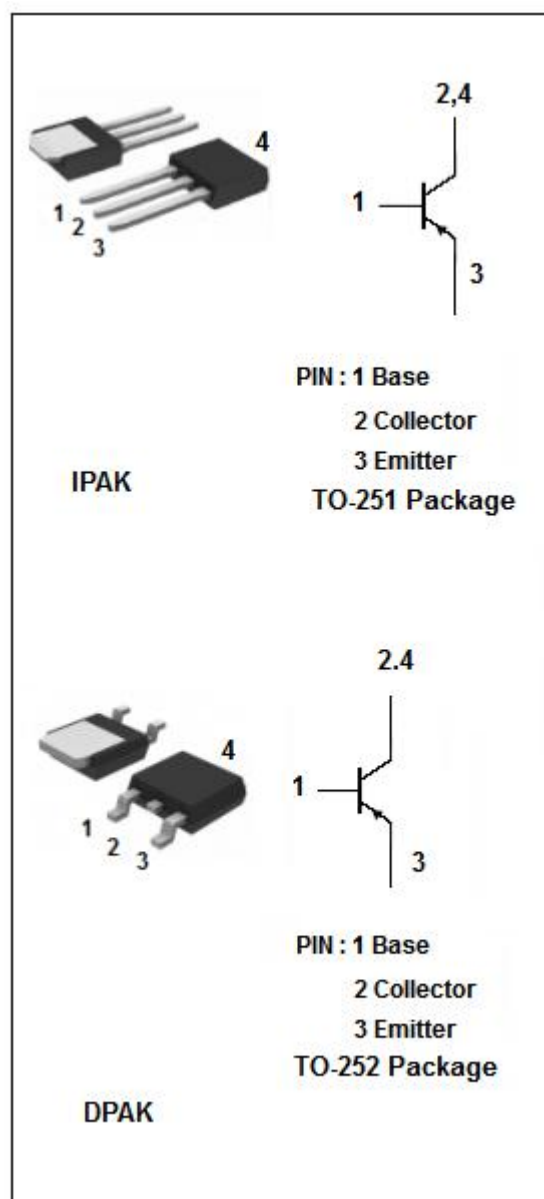
- Large current capacitance
- High-speed switching
- 100% avalanche tested
- High allowable power dissipation
- Minimum Lot-to-Lot variations for robust device performance and reliable operation
- Complementary to 2SC5707

## APPLICATIONS

- DC/DC converter, relay drivers, lamp drivers, motor drivers, flash

ABSOLUTE MAXIMUM RATINGS ( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-50	V
$V_{CEO}$	Collector-Emitter Voltage	-50	V
$V_{EBO}$	Emitter-Base Voltage	-6	V
$I_C$	Collector Current-Continuous	-8	A
$I_{CM}$	Collector Current-Peak	-11	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	15	W
	Collector Power Dissipation @ $T_a=25^\circ\text{C}$	1.0	
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

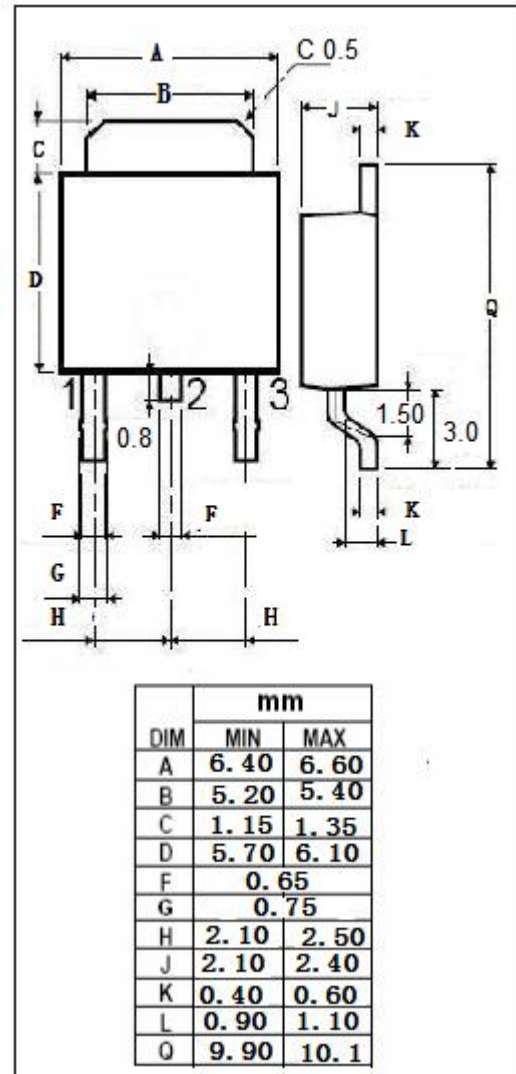
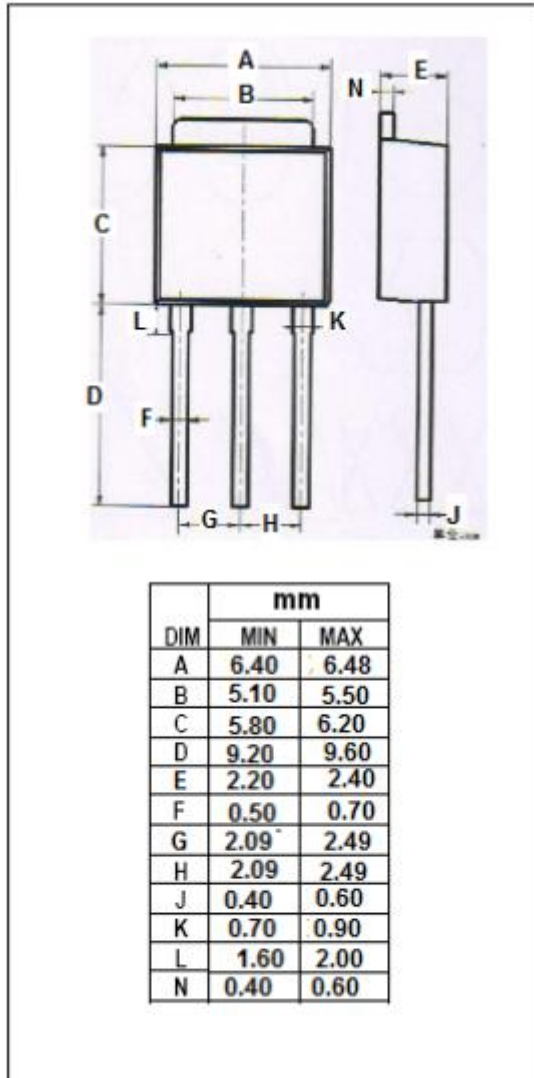
T<sub>c</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)-1</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -3.5A; I <sub>B</sub> = -175mA			-0.390	V
V <sub>CE(sat)-2</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = -2.0A; I <sub>B</sub> = -40mA			-0.4	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = -2.0A; I <sub>B</sub> = -40mA			-1.2	V
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -1mA; I <sub>B</sub> = 0	-50			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -10μA; I <sub>C</sub> = 0	-6			V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = -40V; I <sub>E</sub> = 0			-0.1	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = -4V; I <sub>C</sub> = 0			-0.1	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = -0.5A; V <sub>CE</sub> = -2V	200		560	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = -10V; f= 1.0MHz		50		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = -500mA; V <sub>CE</sub> = -10V		290		MHz

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**Outline Drawing**



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